

## Silicon NPN Power Transistors

2SC1034

## DESCRIPTION

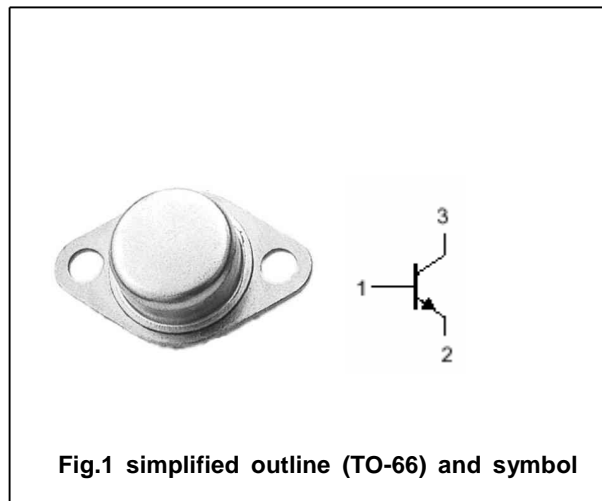
- With TO-66 package
- High breakdown voltage

## APPLICATIONS

- For horizontal deflection output applications

## PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings( $T_a=?$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	1100	V
$V_{EBO}$	Emitter-base voltage	Open collector	13	V
$I_C$	Collector current		1	A
$P_C$	Collector power dissipation	$T_C=25?$	25	W
$T_j$	Junction temperature		150	?
$T_{stg}$	Storage temperature		-65~150	?

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## CHARACTERISTICS

T<sub>j</sub>=25? unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =10mA; I <sub>E</sub> =0	1100			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =5mA; I <sub>C</sub> =0	13			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =750mA; I <sub>B</sub> =75m A			5.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =750mA; I <sub>B</sub> =75m A			1.4	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =50V; I <sub>E</sub> =0			0.2	mA
		V <sub>CB</sub> =800V; I <sub>E</sub> =0			5.0	
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =8V; I <sub>C</sub> =0			4	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =750mA ; V <sub>CE</sub> =3V	4		40	
f <sub>T</sub>	Transition frequency	I <sub>E</sub> =-0.2A ; V <sub>CE</sub> =10V		5		MHz
C <sub>ob</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =10V; f=1MHz		95		pF

PACKAGE OUTLINE

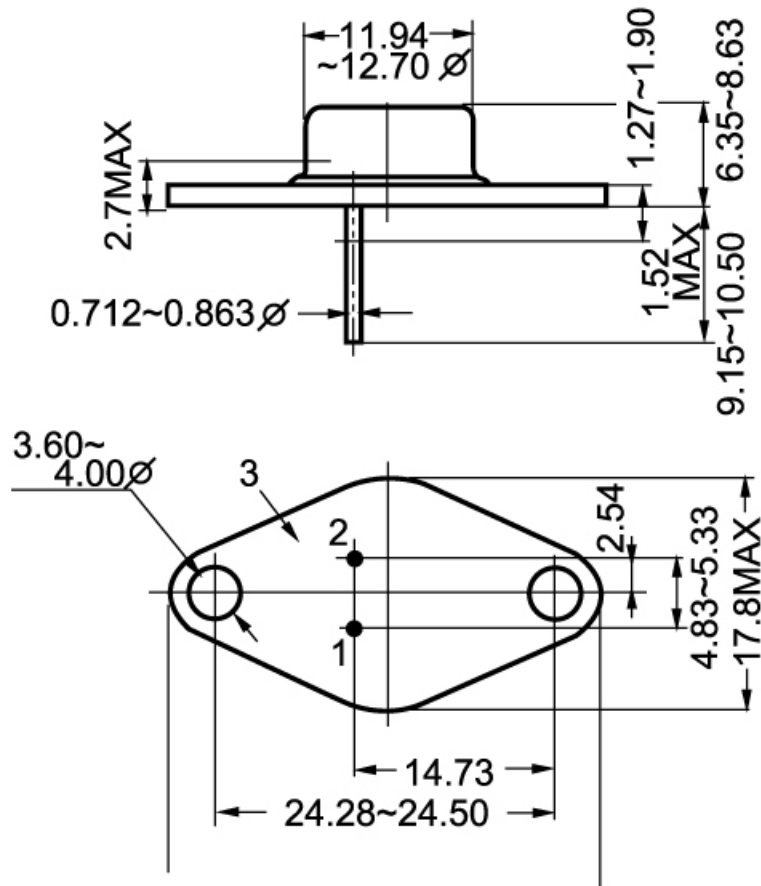


Fig.2 outline dimensions